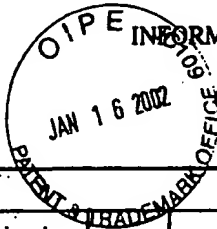


37 CFR 1.501

INFORMATION DISCLOSURE STATEMENT  
IN A PATENT

(use several sheets if necessary)

Patent No.  
P99,1696Serial No.  
09/381,323Applicants  
Thomas Aeugle, et al.Filing Date  
09/16/1999Group Art Unit  
2827

## U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
TYT	AA	5,208,172	05-04-93	J. Fitch, et al.	—	—	—
TYT	AB	5,545,586	08-13-96	R. Koh	—	—	—
TYT	AC	5,376,562	12-27-94	J. Fitch, et al.	—	—	—
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
TYT	AL	EP 0 268 941	06-01-88	Europe	—	—	Abstract	X
TYT	AM	EP 0 430 514	06-05-91	Europe	—	—		X
TYT	AN	DE 196 21 244	11-14-96	Germany	—	—	Abstract	X
	AO							
	AP							
	AQ							

## OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

TYT	AR	R. Loo, et al., "Vertical Si p-MOS transistor selectively grown by low pressure chemical vapour deposition", Thin Solid Films, Vol. 294, p. 267 (1997)
TYT	AS	D. Behammer, "Selectively grown vertical Si-p MOS transistor with short channel lengths", Electronics Letters, Vol. 32, No. 4, p. 406 (15 February 1996)
TYT	AT	L. Risch, et al., "Vertical MOS Transistors with 70 nm Channel Length", ESSDERC 1995, p. 101
TYT	AU	"Roadmap for Semiconductors", Solid State Technology, Vol. 3, February 1995, pp. 42
TYT	AV	A. Hori, et al., "A 0.05 $\mu$ m-CMOS with Ultra Shallow Source/Drain Junctions Fabricated by SKeV Ion Implantation and Rapid Thermal Annealing", IEDM 94 p. 485
TYT	AW	H. Hu, et al., "Channel and Source/Drain Engineering in High-Performance Sub-0.1 $\mu$ m NMOSFETs Using X-Ray Lithography", 1994 Symposium on VLSI Technology Digest of Technical Papers, p. 17
TYT	AX	L. Vescan, "Radiative Recombination in SiGe/Si Dots and Wires Selectively Grown by LPCVD", Material Science and Engineering, Vol. 28, p. 173 (1994)

Examiner  
Thanh TranDate Considered  
06/17/04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.